4-Bit Dual-Supply Non-Inverting Level Translator

The NLSV4T244 is a 4-bit configurable dual-supply voltage level translator. The input A_n and output B_n ports are designed to track two different power supply rails, V_{CCA} and V_{CCB} respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input A_n to the output B_n port.

Features

- Wide V_{CCA} and V_{CCB} Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential V_{CCA} and V_{CCB} Sequencing
- Outputs at 3-State until Active V_{CC} is Reached
- Power-Off Protection
- Outputs Switch to 3-State with V_{CCB} at GND
- Ultra-Small Packaging: 1.7 mm x 2.0 mm UQFN12
- NLVSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb–Free Devices

Typical Applications

• Mobile Phones, PDAs, Other Portable Devices

Important Information

 ESD Protection for All Pins: HBM (Human Body Model) > 1500 V



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MARKING DIAGRAMS



UQFN12 MU SUFFIX CASE 523AE



UR = Specific Device Code

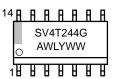
M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

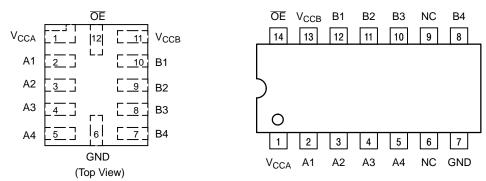


Figure 1. Pin Assignments

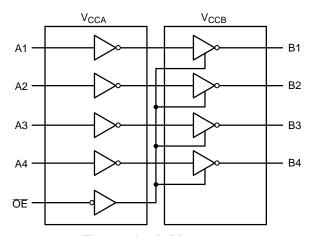


Figure 2. Logic Diagram

PIN ASSIGNMENT

PIN	FUNCTION
V _{CCA}	Input Port DC Power Supply
V _{CCB}	Output Port DC Power Supply
GND	Ground
A _n	Input Port
B _n	Output Port
ŌĒ	Output Enable

TRUTH TABLE

In	Inputs				
ŌĒ	A _n	B _n			
L	L	L			
L	Н	Н			
Н	Х	3-State			

ORDERING INFORMATION

Device	Package	Shipping [†]
NLSV4T244MUTAG	UQFN12	2000 / Tone and Deal
NLVSV4T244MUTAG*	(Pb-Free)	3000 / Tape and Reel
NLSV4T244DR2G	SOIC-14 (Pb-Free)	2500 / Tape and Reel
NLSV4T244DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape and Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

^{*}NLVSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MAXIMUM RATINGS

Symbol	Rating		Value	Condition	Unit
V _{CCA} , V _{CCB}	DC Supply Voltage		-0.5 to +5.5		V
VI	DC Input Voltage	A _n	-0.5 to +5.5		V
V _C	Control Input	OE	-0.5 to +5.5		V
Vo	DC Output Voltage (Power Down)	B _n	-0.5 to +5.5	$V_{CCA} = V_{CCB} = 0$	V
	(Active Mode)	B _n	-0.5 to +5.5		V
	(Tri–State Mode)	B _n	-0.5 to +5.5		V
I _{IK}	DC Input Diode Current		-20	V _I < GND	mA
lok	DC Output Diode Current		-50	V _O < GND	mA
Io	DC Output Source/Sink Current		±50		mA
I _{CCA} , I _{CCB}	DC Supply Current Per Supply Pin		±100		mA
I _{GND}	DC Ground Current per Ground Pin		±100		mA
T _{STG}	Storage Temperature		-65 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CCA} , V _{CCB}	Positive DC Supply Voltage		0.9	4.5	V
VI	Bus Input Voltage		GND	4.5	V
V_{C}	Control Input	ŌĒ	GND	4.5	V
V_{IO}	Bus Output Voltage (Power Down Mode)	B _n	GND	4.5	V
	(Active Mode)	B _n	GND	V _{CCB}	V
	(Tri–State Mode)	B _n	GND	4.5	V
T_A	Operating Temperature Range		-40	+105	°C
Δt / ΔV	Input Transition Rise or Rate V_{I} , from 30% to 70% of V_{CC} ; V_{CC} = 3.3 V \pm 0.3 V	0	10	nS	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

					-40°C to	o +85°C	
Symbol	Parameter	Test Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Unit
V _{IH}	Input HIGH Voltage		3.6 – 4.5	0.9 – 4.5	2.2	-	V
	(An, \overline{OE})		2.7 – 3.6		2.0	-	
			2.3 – 2.7		1.6	-	
			1.4 – 2.3		0.65 * V _{CCA}	-	
			0.9 – 1.4		0.9 * V _{CCA}	-	
V _{IL}	Input LOW Voltage		3.6 – 4.5	0.9 – 4.5	-	0.8	V
	(An, \overline{OE})		2.7 – 3.6		_	0.8	
			2.3 – 2.7		-	0.7	
			1.4 – 2.3		-	0.35 * V _{CCA}	
			0.9 – 1.4		-	0.1 * V _{CCA}	
V _{OH}	Output HIGH Voltage	$I_{OH} = -100 \mu A; V_I = V_{IH}$	0.9 – 4.5	0.9 – 4.5	V _{CCB} - 0.2	-	V
		$I_{OH} = -0.5 \text{ mA}; V_I = V_{IH}$	0.9	0.9	0.75 * V _{CCB}	-	
		$I_{OH} = -2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	1.05	-	
		$I_{OH} = -6 \text{ mA}; V_I = V_{IH}$	1.65	1.65	1.25	-	
			2.3	2.3	2.0	-	
		$I_{OH} = -12 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.8	-	
			2.7	2.7	2.2	-	
		$I_{OH} = -18 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.7	-	
			3.0	3.0	2.4	-	
		$I_{OH} = -24 \text{ mA}; V_I = V_{IH}$	3.0	3.0	2.2	-	
V _{OL}	Output LOW Voltage	$I_{OL} = 100 \mu A; V_I = V_{IL}$	0.9 – 4.5	0.9 – 4.5	_	0.2	V
		$I_{OL} = 0.5 \text{ mA}; V_I = V_{IL}$	1.1	1.1	-	0.3	
		$I_{OL} = 2 \text{ mA}; V_I = V_{IL}$	1.4	1.4	_	0.35	
		$I_{OL} = 6 \text{ mA}; V_I = V_{IL}$	1.65	1.65	-	0.3	
		$I_{OL} = 12 \text{ mA}; V_I = V_{IL}$	2.3	2.3	-	0.4	
			2.7	2.7	-	0.4	
		$I_{OL} = 18 \text{ mA}; V_I = V_{IL}$	2.3	2.3	-	0.6	
			3.0	3.0	-	0.45	
		I_{OL} = 24 mA; V_I = V_{IL}	3.0	3.0	-	0.6	
I _I	Input Leakage Current	$V_I = V_{CCA}$ or GND	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μΑ
l _{OFF}	Power-Off Leakage Current	OE = 0 V	0 0.9 – 4.5	0.9 – 4.5 0	-1.0 -1.0	1.0 1.0	μΑ
I _{CCA}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μΑ
I _{CCB}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μΑ
_{CA} + I _{CCB}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	4.0	μΑ
ΔI_{CCA}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μΑ
ΔI_{CCB}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μΑ
l _{OZ}	I/O Tri–State Output Leakage	$T_A = 25^{\circ}C, \overline{OE} = V_{CCA}$	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TOTAL STATIC POWER CONSUMPTION ($I_{CCA} + I_{CCB}$)

					-40°C to	o +85°C					
					V _{CCI}	_B (V)					
	4.	.5	3	.3	2.	.8	1.	.8	0.	.9	
V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
4.5		2		2		2		2		< 1.5	μΑ
3.3		2		2		2		2		< 1.5	μΑ
2.8		< 2		< 1		< 1		< 0.5		< 0.5	μΑ
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	μΑ
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	μΑ

NOTE: Connect ground before applying supply voltage V_{CCA} or V_{CCB}. This device is designed with the feature that the power–up sequence of V_{CCA} and V_{CCB} will not damage the IC.

AC ELECTRICAL CHARACTERISTICS

							-40°C t	o +85°C					
							V _{CC}	_B (V)					
			4.	.5	3	.3	2	.8	1	.8	1.	.2	
Symbol	Parameter	V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation	4.5		1.6		1.8		2.0		2.1		2.3	nS
t _{PHL} (Note 1)	Delay,	3.3		1.7		1.9		2.1		2.3		2.6	
(Note 1)	A _n to B _n	2.8		1.9		2.1		2.3		2.5		2.8	
		1.8		2.1		2.4		2.5		2.7		3.0	
		1.2		2.4		2.7		2.8		3.0		3.3	
t _{PZH} ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t _{PZL} (Note 1)	Enable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note 1)	OE to B _n	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t _{PHZ} ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t _{PLZ}	Disable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note 1)	OE to B _n	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t _{OSHL} , Output to	4.5		0.15		0.15		0.15		0.15		0.15	nS	
toslh	Output	3.3		0.15		0.15		0.15		0.15		0.15	
(Note 1)		2.5		0.15		0.15		0.15		0.15		0.15	
		1.8		0.15		0.15		0.15		0.15		0.15	
		1.2		0.15		0.15		0.15		0.15		0.15	

^{1.} Propagation delays defined per Figure 3.

CAPACITANCE

Symbol	Parameter	Test Conditions	Typ (Note 2)	Unit
C _{IN}	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF
C _{I/O}	I/O Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF
C _{PD}	Power Dissipation Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA}, f = 10 \text{ MHz}$	20	pF

Typical values are at T_A = +25°C.
 C_{PD} is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I_{CC(operating)} ≅ C_{PD} x V_{CC} x f_{IN} x N_{SW} where I_{CC} = I_{CCA} + I_{CCB} and N_{SW} = total number of outputs switching.

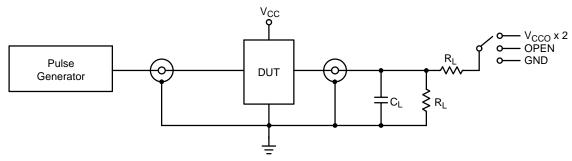


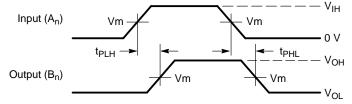
Figure 3. AC (Propagation Delay) Test Circuit

Test	Switch
t _{PLH} , t _{PHL}	OPEN
t _{PLZ} , t _{PZL}	V _{CCO} x 2
t _{PHZ} , t _{PZH}	GND

C_L = 15 pF or equivalent (includes probe and jig capacitance)

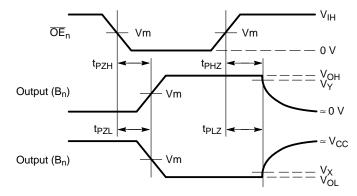
 $R_L = 2 k\Omega$ or equivalent

 Z_{OUT} of pulse generator = 50 Ω



Waveform 1 – Propagation Delays

 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



Waveform 2 - Output Enable and Disable Times

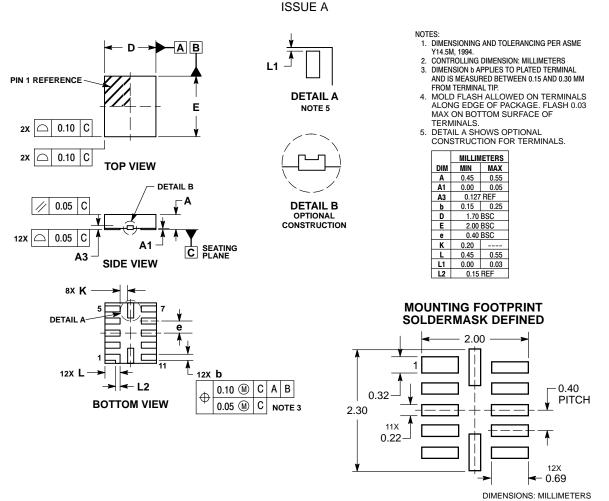
 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$

Figure 4. AC (Propagation Delay) Test Circuit Waveforms

	V _{CC}							
Symbol	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V			
V_{mA}	V _{CCA} /2							
V _{mB}	V _{CCB} /2							
V _X	V _{OL} + 10% V _{OH}							
V_{Y}	V _{OH} x 0.9							

PACKAGE DIMENSIONS

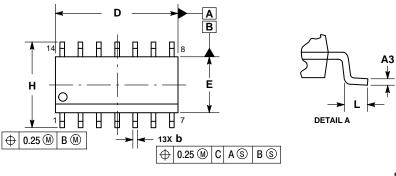
UQFN12 1.7x2.0, 0.4P CASE 523AE

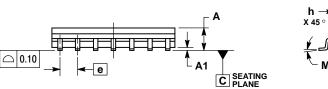


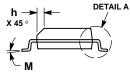
^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE L**







NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

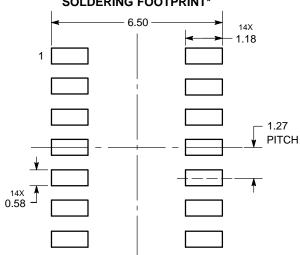
 3. DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.

 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.

 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.25 0.50 0.010		0.019
L	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

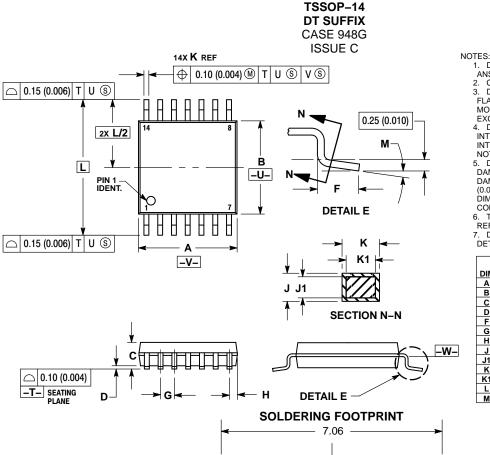
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

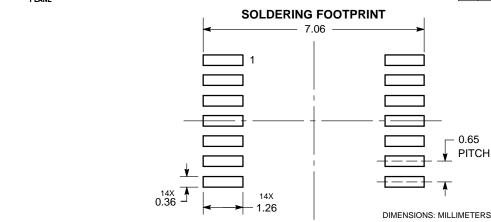


- DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD LASH, PROTRUSIONS OR GATE BURRS MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–. TERMINAL NUMBERS ARE SHOWN FOR

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0°	8 °



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